





20V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

| DV | D Mov | I _D Max | |
|-------------------|--------------------------------|------------------------|--|
| BV _{DSS} | R _{DS(ON)} Max | T _A = +25°C | |
| 20V | 0.99Ω @ V _{GS} = 4.5V | 0.54A | |
| | 1.2Ω @ V _G S = 2.5V | 0.49A | |
| | 1.8Ω @ V _{GS} = 1.8V | 0.4A | |
| | 2.4Ω @ V _G S = 1.5V | 0.35A | |

Description and Applications

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

Features and Benefits

- Low Package Profile
- 0.6mm x 0.4mm Package Footprint
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V Max
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
 - For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

 https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: X2-DFN0604-3
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.001 grams (Approximate)

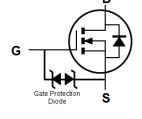












Top View Package Pin Configuration

Equivalent Circuit

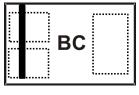
Ordering Information (Note 4)

| Part Number | Case | Packaging | |
|---------------|--------------|-----------------|--|
| DMN2991UFO-7B | X2-DFN0604-3 | 10k/Tape & Reel | |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



BC= Product Type Marking Code Bar Denotes Gate and Source Side

Top View



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | | |
|--|--------|------------------------|------------------|------|-----|
| Drain-Source Voltage | | | V _{DSS} | 20 | V |
| Gate-Source Voltage | Vgss | ±8 | V | | |
| Continuous Drain Current (Note 5) \/ 45\/ | Steady | T _A = +25°C | - I _D | 0.54 | - A |
| Continuous Drain Current (Note 5) V _{GS} = 4.5V | State | T _A = +85°C | | 0.43 | |
| Pulsed Drain Current (Note 6) | | | I _{DM} | 1.2 | А |

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | |
|--|--------------|----------------|-------------|------|
| Total Power Dissipation (Note 5) | Steady State | P _D | 0.44 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State | Reja | 281 | °C/W |
| Operating and Storage Temperature Range | | TJ, TSTG | -55 to +150 | °C |

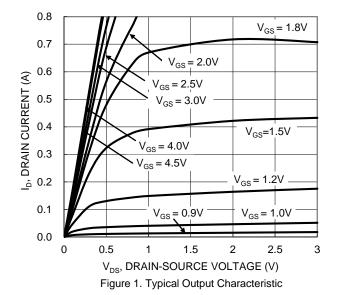
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|-----------------------------------|---------------------|-----|------|------|------|---|--|
| OFF CHARACTERISTICS (Note 7) | | | | | | | |
| Drain-Source Breakdown Voltage | BVDSS | 20 | _ | _ | V | $V_{GS} = 0V, I_D = 250\mu A$ | |
| Zero Gate Voltage Drain Current | I _{DSS} | _ | _ | 1 | μA | V _{DS} = 16V, V _{GS} = 0V | |
| Gate-Source Leakage | Igss | _ | _ | ±10 | μA | $V_{GS} = \pm 5V$, $V_{DS} = 0V$ | |
| ON CHARACTERISTICS (Note 7) | | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | 0.4 | 1 | 1.0 | V | $V_{DS} = V_{GS}$, $I_D = 250\mu A$ | |
| | | l | 0.5 | 0.99 | Ω | $V_{GS} = 4.5V, I_{D} = 100mA$ | |
| Static Drain-Source On-Resistance | Proyent | | 0.6 | 1.2 | | $V_{GS} = 2.5V, I_{D} = 50mA$ | |
| Static Drain-Source On-Nesistance | RDS(ON) | _ | 0.8 | 1.8 | | $V_{GS} = 1.8V, I_D = 20mA$ | |
| | | _ | 1.0 | 2.4 | | $V_{GS} = 1.5V, I_D = 10mA$ | |
| Diode Forward Voltage | VsD | _ | 0.7 | 1.0 | V | V _G S = 0V, I _S = 150mA | |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | • | | |
| Input Capacitance | Ciss | _ | 21.5 | _ | pF | V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz | |
| Output Capacitance | Coss | _ | 4.9 | _ | pF | | |
| Reverse Transfer Capacitance | Crss | _ | 3.7 | _ | pF | 1 – 1.000112 | |
| Gate Resistance | Rg | _ | 0.94 | _ | Ω | $V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$ | |
| Total Gate Charge | Qg | _ | 0.35 | _ | nC | V _{GS} = 4.5V, V _{DS} = 10V, -I _D = 250mA | |
| Gate-Source Charge | Qgs | | 0.07 | _ | nC | | |
| Gate-Drain Charge | Qgd | | 0.08 | _ | nC | | |
| Turn-On Delay Time | td(on) | | 5.6 | _ | ns | $\begin{aligned} &V_{DD}=10V,V_{GS}=4.5V,\\ &R_{L}=47\Omega,R_{g}=10\Omega,\\ &I_{D}=200mA \end{aligned}$ | |
| Turn-On Rise Time | t _R | | 4.9 | _ | ns | | |
| Turn-Off Delay Time | tD(OFF) | _ | 60.6 | _ | ns | | |
| Turn-Off Fall Time | tF | _ | 27.6 | _ | ns | | |

Notes:

- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





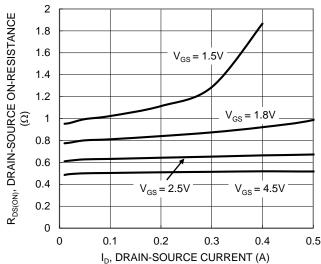


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

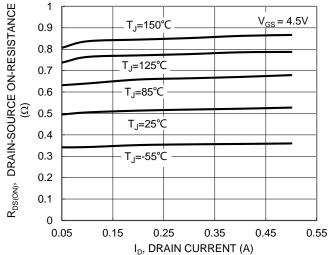


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

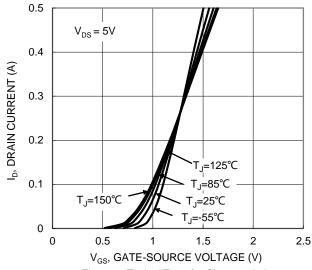


Figure 2. Typical Transfer Characteristic

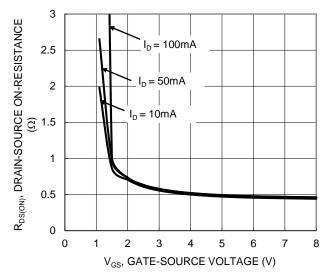


Figure 4. Typical Transfer Characteristic

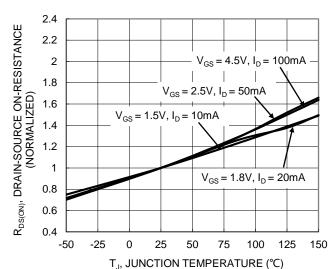


Figure 6. On-Resistance Variation with Junction Temperature



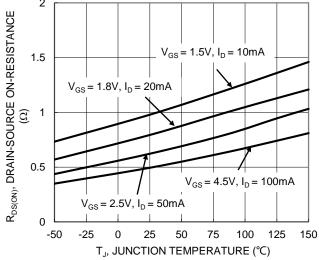
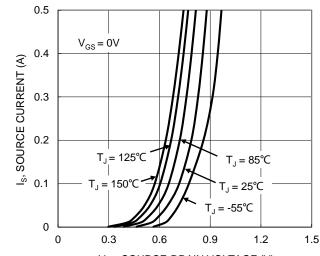


Figure 7. On-Resistance Variation with Junction Temperature



V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

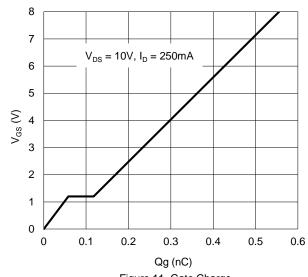


Figure 11. Gate Charge

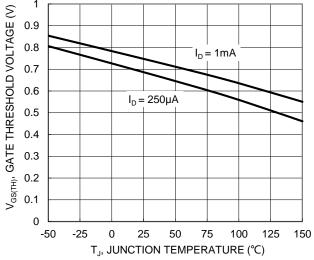
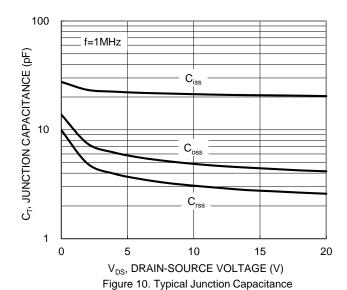


Figure 8. Gate Threshold Variation vs. Junction Temperature





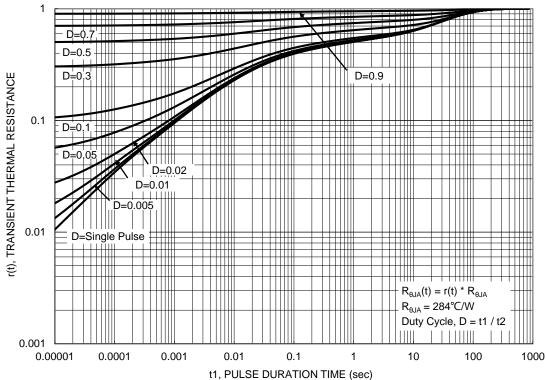


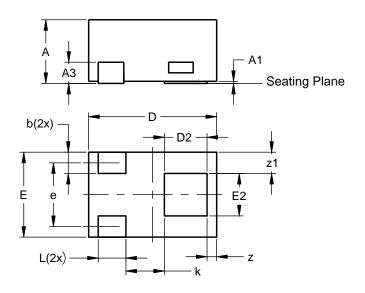
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN0604-3

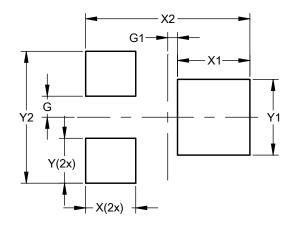


| X2-DFN0604-3 | | | | | |
|----------------------|------|------|-------|--|--|
| Dim | Min | Max | Тур | | |
| Α | | 0.40 | 0.36 | | |
| A1 | 0.00 | 0.03 | 0.02 | | |
| A3 | | | 0.10 | | |
| b | 0.07 | 0.15 | 0.10 | | |
| D | 0.55 | 0.65 | 0.60 | | |
| D2 | 0.15 | 0.25 | 0.20 | | |
| Е | 0.35 | 0.45 | 0.40 | | |
| E2 | 0.15 | 0.25 | 0.20 | | |
| e | | | 0.30 | | |
| k | 0.15 | | | | |
| L | 0.10 | 0.18 | 0.13 | | |
| Z | | | 0.045 | | |
| z1 | | | 0.10 | | |
| All Dimensions in mm | | | | | |

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN0604-3



| Dimensions | Value (in mm) |
|------------|---------------|
| G | 0.075 |
| G1 | 0.035 |
| Х | 0.180 |
| X1 | 0.260 |
| X2 | 0.590 |
| Y | 0.160 |
| Y1 | 0.270 |
| Y2 | 0.470 |



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